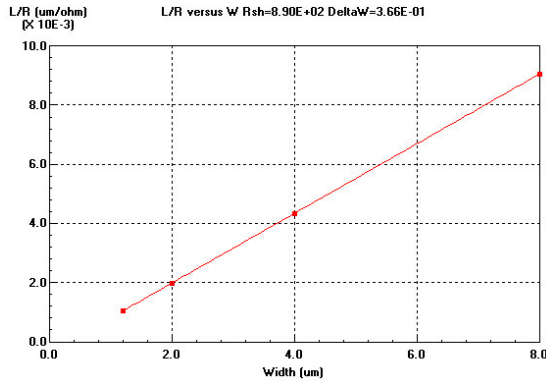


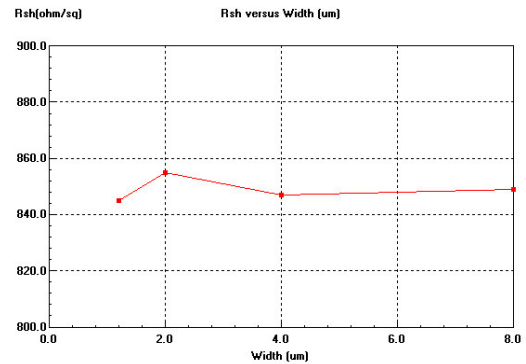


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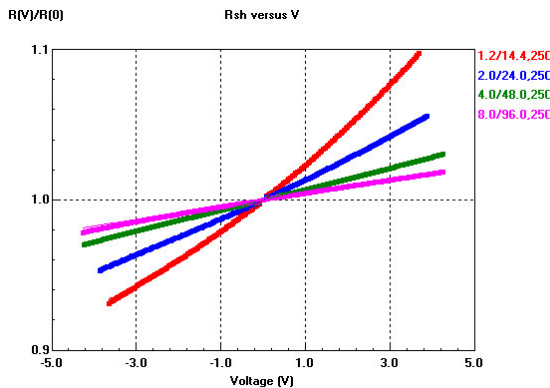
Doc. TD-LO18-SP-2003	No.:	Doc. Title: 0.18um Logic Low Leakage 1P6M (1P5M, 1P4M) Salicide 1.8V/5.0V SPICE Model (Version 1.3)	Doc. Rev: 4R	Tech Dev Rev.:1.3	Page 1/21	No.:
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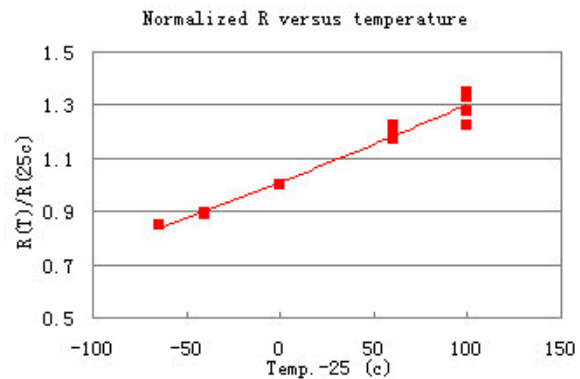
Fit.D1(a) Length/Resistance versus width for sheet resistance and delta width's extraction



Fit.D1(b) Extracted sheet resistance versus width for recommend width's selection



Fit.D1(c) Simulated(lines) and measured(symbols) resistance which normalized to Rsh(V=0) versus voltage.



Fit.D1(d) Sheet resistance which normalized to Rsh(T=25C) for various widths. (Tc1 = 2.73E-03, Tc2 = 1.65E-06)

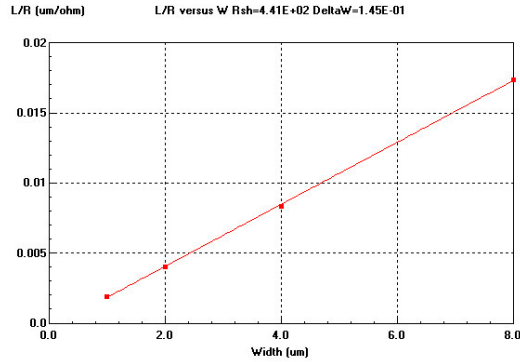
Fig.D1(a)(b)(c)(d) Fitting results of Nwell under STI resistance model

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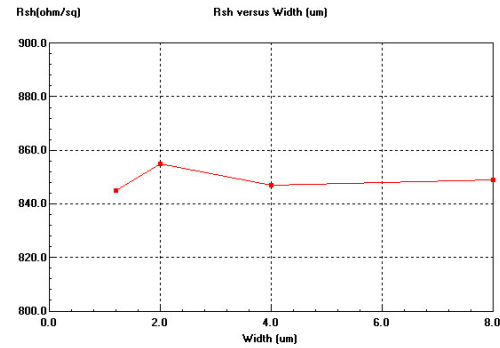


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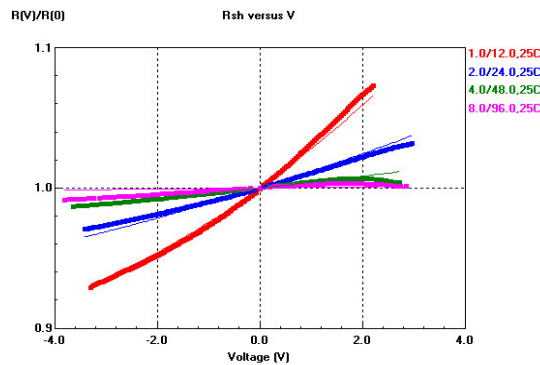
Doc. TD-LO18-SP-2003	No.: Doc. Title: 0.18um Logic Low Leakage 1P6M (1P5M, 1P4M) Salicide 1.8V/5.0V SPICE Model (Version 1.3)	Doc. Rev: 4R	Tech Dev Rev.:1.3	Page 2/21	No.:
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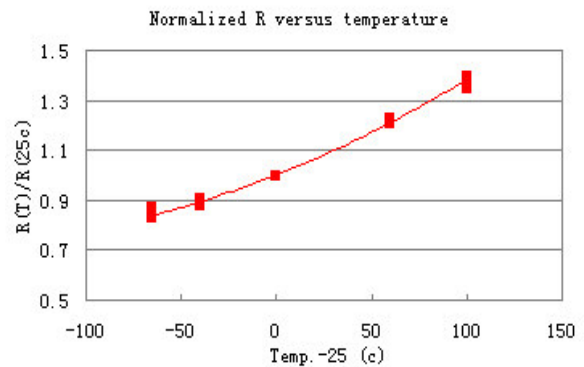
Fit.D2(a) Length/Resistance versus width for sheet resistance and delta width's extraction



Fit.D2(b) Extracted sheet resistance versus width for recommend width's selection



Fit.D2(c) Simulated(lines) and measured(symbols) resistance which normalized to Rsh(V=0) versus voltage.



Fit.D2(d) Sheet resistance which normalized to Rsh(T=25C) for various widths.
(Tc1 = 3.02E-03, Tc2 = 8.06E-06)

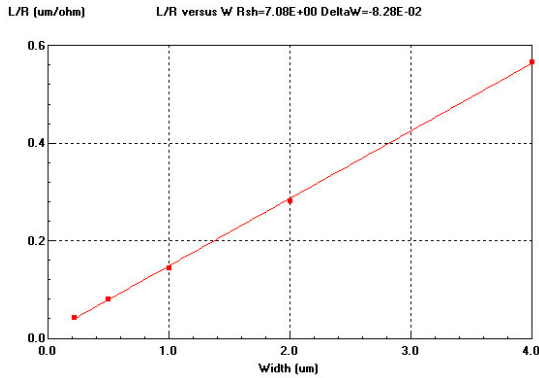
Fig.D2(a)(b)(c)(d) Fitting results of Nwell under AA resistance model

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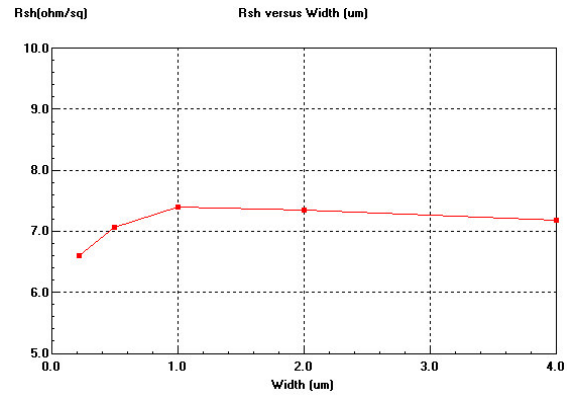


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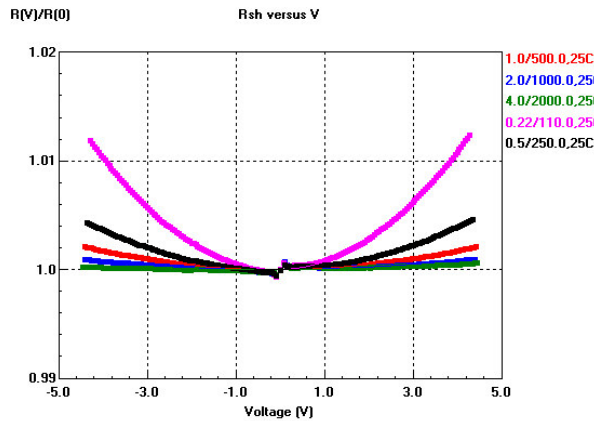
Doc. TD-LO18-SP-2003	No.:	Doc. Title: 0.18um Logic Low Leakage 1P6M (1P5M, 1P4M) Salicide 1.8V/5.0V SPICE Model (Version 1.3)	Doc. Rev: 4R	Tech Dev Rev.:1.3	Page 3/21	No.:
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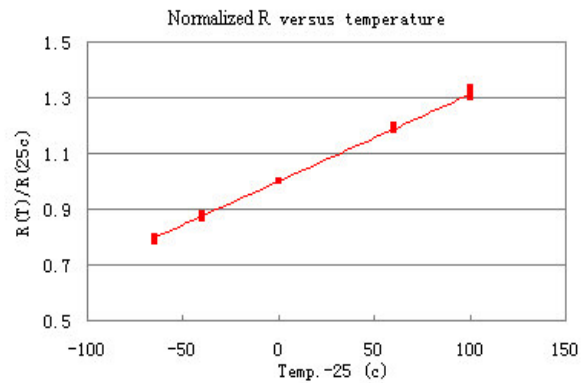
Fit.D3(a) Length/Resistance versus width for sheet resistance and delta width's extraction



Fit.D3(b) Extracted sheet resistance versus width for recommend width's selection



Fit.D3(c) Simulated(lines) and measured(symbols) resistance which normalized to Rsh(V=0) versus voltage.



Fit.D3(d) Sheet resistance which normalized to Rsh(T=25C) for various widths.
(Tc1 = 3.12E-03, Tc2 = 3.022E-08)

Fig.D3(a)(b)(c)(d) Fitting results of N+ Diffusion with silicide resistance model

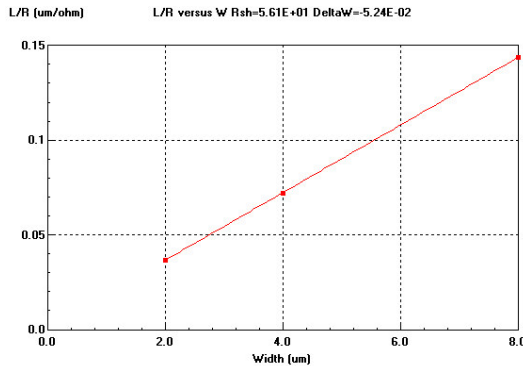
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According to: Document Control Procedure; Attachment No.: QR-QUSM-02-2001-002; Rev.:0

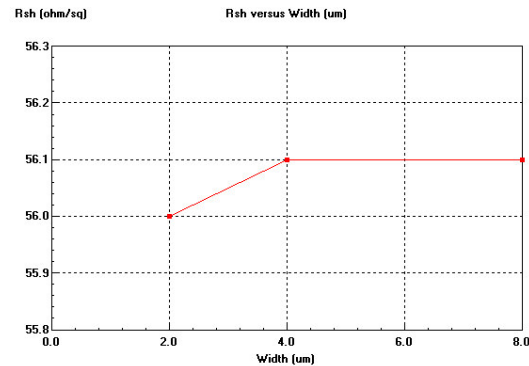


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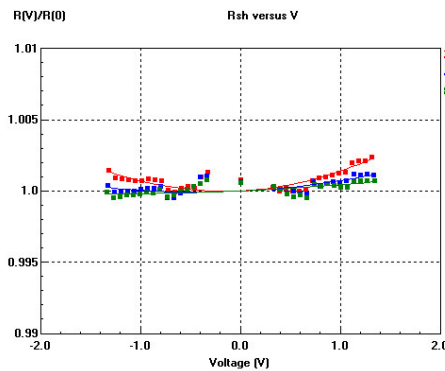
Doc. TD-LO18-SP-2003	No.: Doc. Title: 0.18um Logic Low Leakage 1P6M (1P5M, 1P4M) Salicide 1.8V/5.0V SPICE Model (Version 1.3)	Doc. Rev: 4R	Tech Dev Rev.:1.3	Page 4/21	No.:
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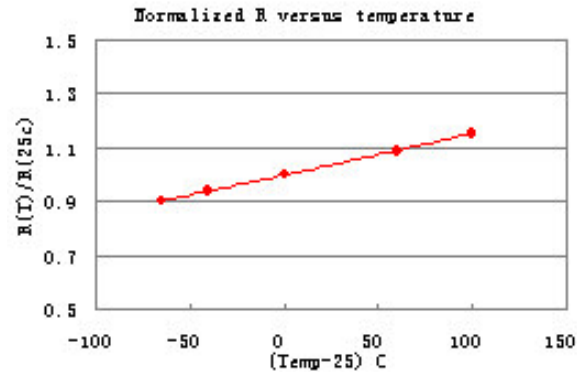
Fit.D4(a) Length/Resistance versus width for sheet resistance and delta width's extraction



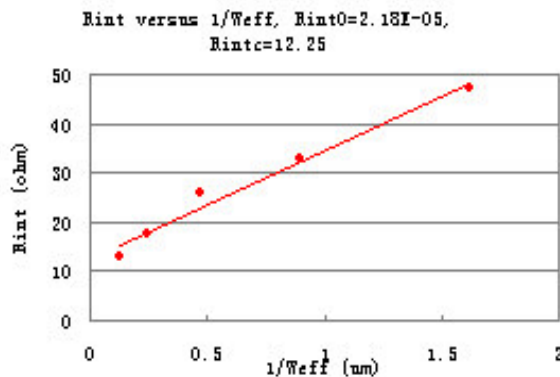
Fit.D4(b) Extracted sheet resistance versus width for recommend width's selection



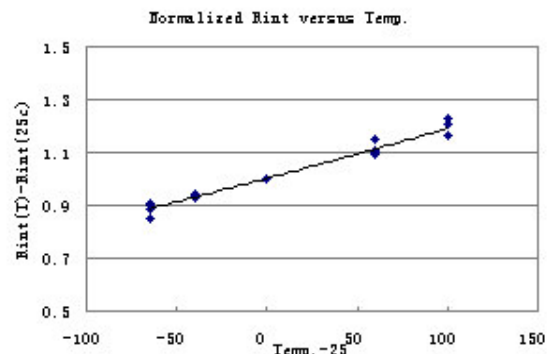
Fit.D4(c) Simulated(lines) and measured(symbols) resistance which normalized to Rsh(V=0) versus voltage.



Fit.D4(d) Sheet resistance which normalized to Rsh(T=25C) for various widths.
(Tc1 = 1.51E-03, Tc2 = 4.22E-07)



Fit.D4(e) Interface resistance versus 1/Weff for the parameter of Rint0 and Rintc's extraction.



Fit.D4(f) Interface resistance which normalized to Rint(T=25C) for various widths.
(Rinttc1= 1.81E-03, Rinttc2= 7.75E-07)

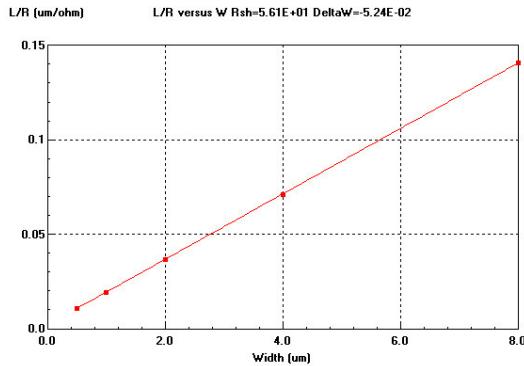
Fig.D4(a)(b)(c)(d)(e)(f) Fitting results of N+ Diffusion without silicide resistance model

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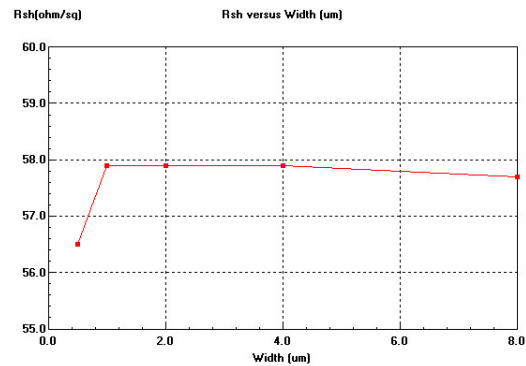


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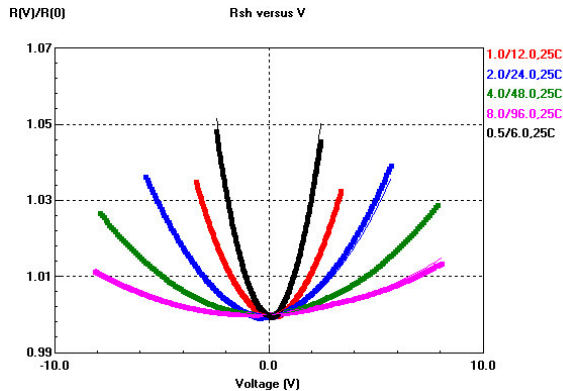
Doc. TD-LO18-SP-2003	No.: Doc. Title: 0.18um Logic Low Leakage 1P6M (1P5M, 1P4M) Salicide 1.8V/5.0V SPICE Model (Version 1.3)	Doc. Rev: 4R	Tech Dev Rev.:1.3	Page 5/21	No.:
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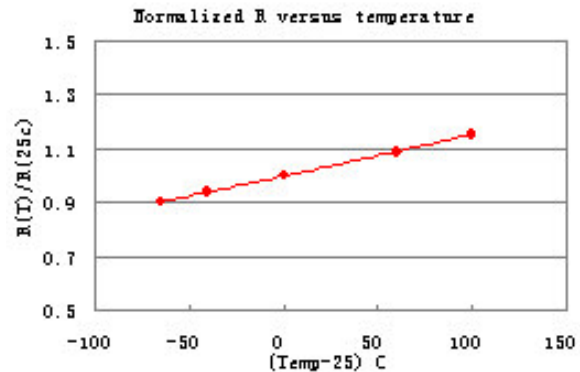
Fit.D5(a) Length/Resistance versus width for sheet resistance and delta width's extraction



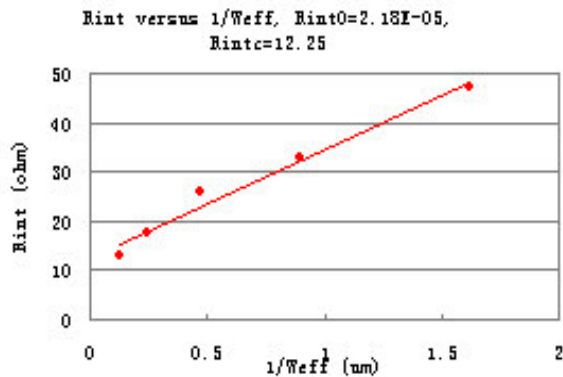
Fit.D5(b) Extracted sheet resistance versus width for recommend width's selection



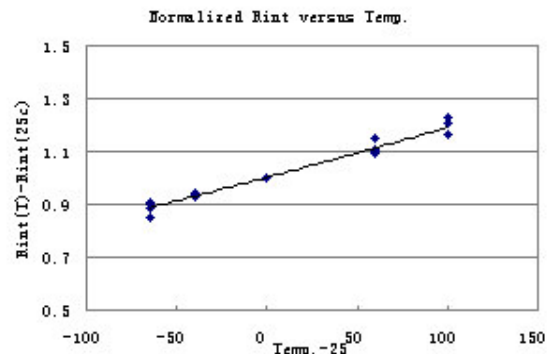
Fit.D5(c) Simulated(lines) and measured(symbols) resistance which normalized to $R_{sh}(V=0)$ versus voltage.



Fit.D5(d) Sheet resistance which normalized to $R_{sh}(T=25C)$ for various widths.
($T_{c1} = 1.51E-03$, $T_{c2} = 4.22E-07$)



Fit.D5(e) Interface resistance versus $1/W_{eff}$ for the parameter of R_{int0} and R_{intc} 's extraction.



Fit.D5(f) Interface resistance which normalized to $R_{int}(T=25C)$ for various widths.
($R_{intc1} = 1.81E-03$, $R_{intc2} = 7.75E-07$)

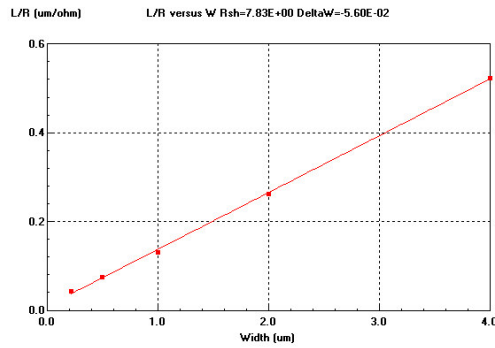
Fig.D5(a)(b)(c)(d)(e)(f) Fitting results of N+ Diffusion without silicide (non-standard) resistance model

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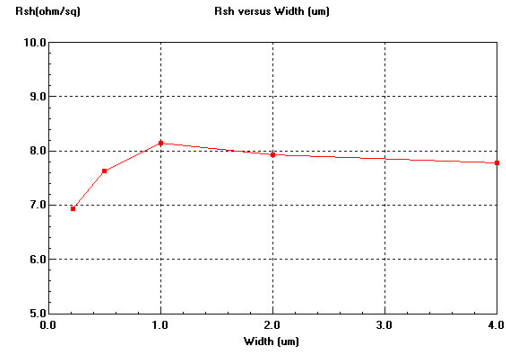


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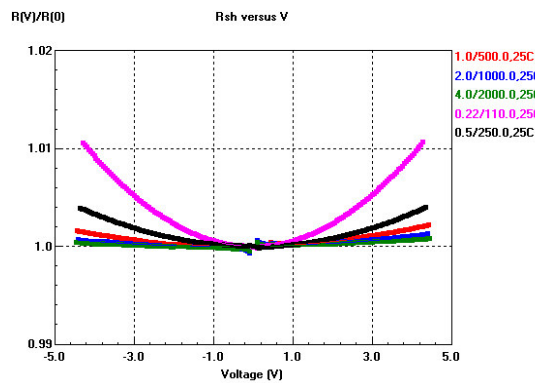
Doc. TD-LO18-SP-2003	No.: Doc. Title: 0.18um Logic Low Leakage 1P6M (1P5M, 1P4M) Salicide 1.8V/5.0V SPICE Model (Version 1.3)	Doc. Rev: 4R	Tech Dev Rev.:1.3	Page 6/21	No.:
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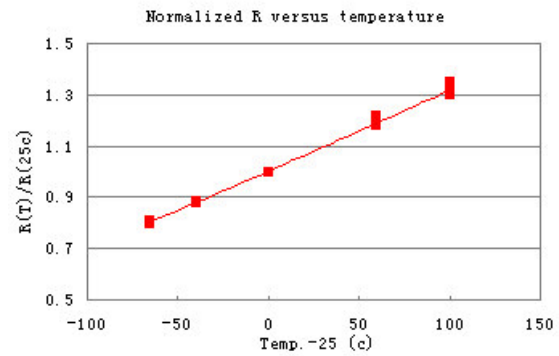
Fit.D6(a) Length/Resistance versus width for sheet resistance and delta width's extraction



Fit.D6(b) Extracted sheet resistance versus width for recommend width's selection



Fit.D6(c) Simulated(lines) and measured(symbols) resistance which normalized to Rsh(V=0) versus voltage.



Fit.D6(d) Sheet resistance which normalized to Rsh(T=25C) for various widths.
(Tc1 = 3.08E-03, Tc2 = 7.034E-07)

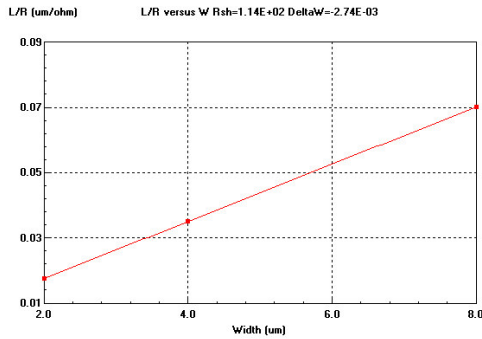
Fig.D6(a)(b)(c)(d) Fitting results of P+ Diffusion with silicide resistance model

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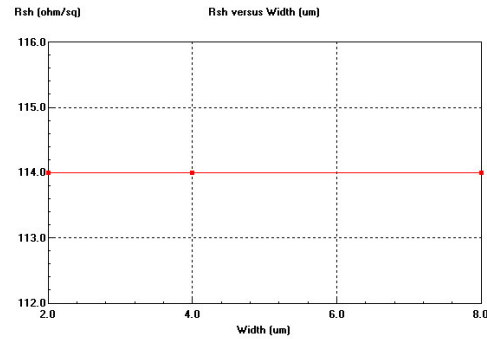


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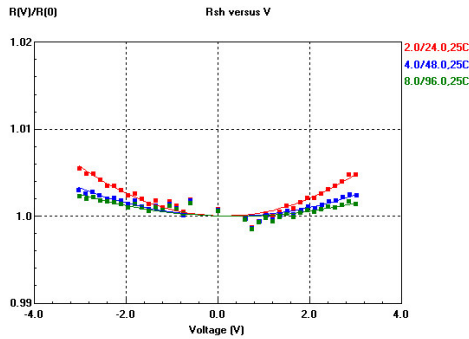
Doc. No.: TD-LO18-SP-2003	Doc. Title: 0.18um Logic Low Leakage 1P6M (1P5M, 1P4M) Salicide 1.8V/5.0V SPICE Model (Version 1.3)	Doc. Rev: 4R	Tech Dev Rev.:1.3	Page No.: 7/21
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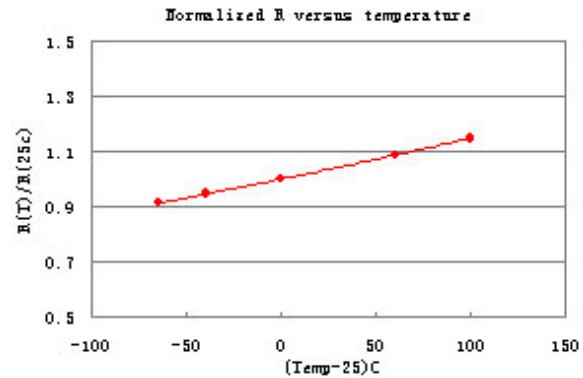
Fit.D7(a) Length/Resistance versus width for sheet resistance and delta width's extraction



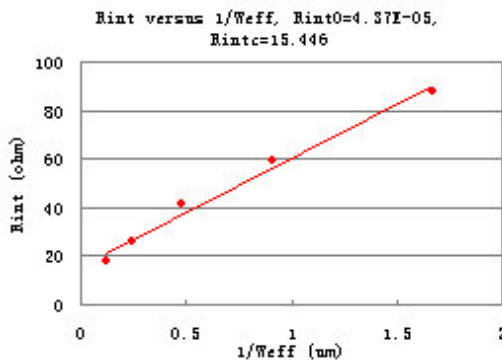
Fit.D7(b) Extracted sheet resistance versus width for recommend width's selection



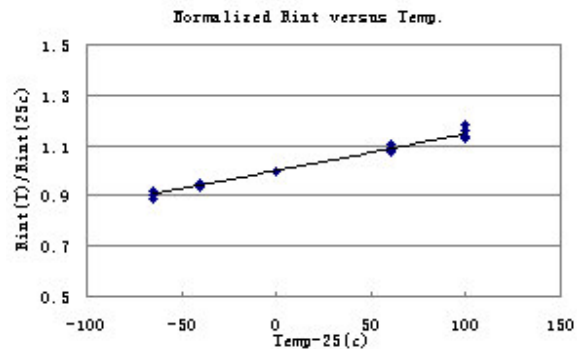
Fit.D7(c) Simulated(lines) and measured(symbols) resistance which normalized to Rsh(V=0) versus voltage.



Fit.D7(d) Sheet resistance which normalized to Rsh(T=25C) for various widths. (Tc1 = 1.41E-03, Tc2 = 6.87E-07)



Fit.D7(e) Interface resistance versus 1/Weff for the parameter of Rint0 and Rintc's extraction



Fit.D7(f) Interface resistance which normalized to Rint(T=25C) for various widths. (Rinttc1= 1.38E-03, Rinttc2 = 6.47E-07)

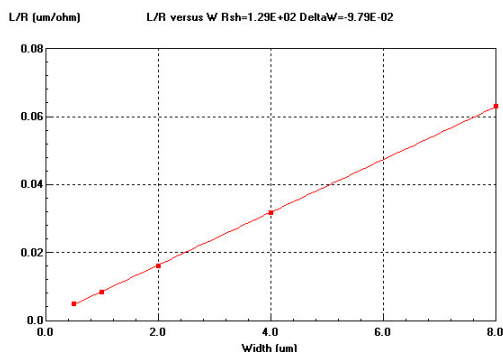
Fig.D7(a)(b)(c)(d)(e)(f) Fitting results of P+ Diffusion without silicide resistance model

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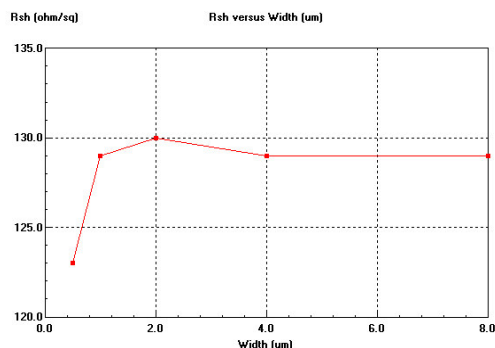


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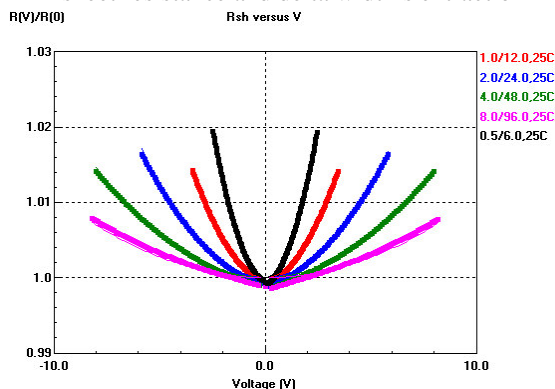
Doc. TD-LO18-SP-2003	No.: Doc. Title: 0.18um Logic Low Leakage 1P6M (1P5M, 1P4M) Salicide 1.8V/5.0V SPICE Model (Version 1.3)	Doc. Rev: 4R	Tech Dev Rev.:1.3	Page 8/21	No.:
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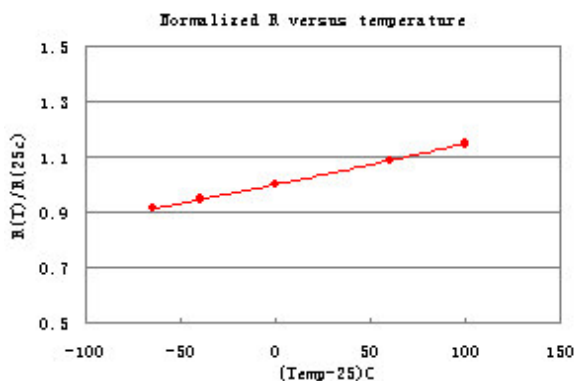
Fit.D8(a) Length/Resistance versus width for sheet resistance and delta width's extraction



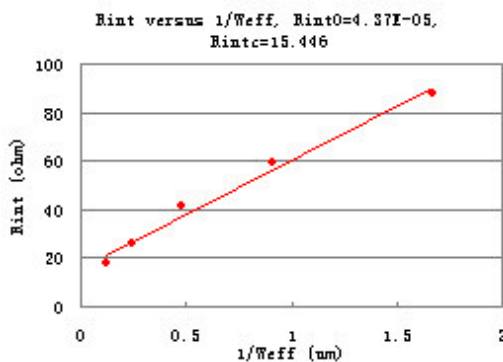
Fit.D8(b) Extracted sheet resistance versus width for recommend width's selection



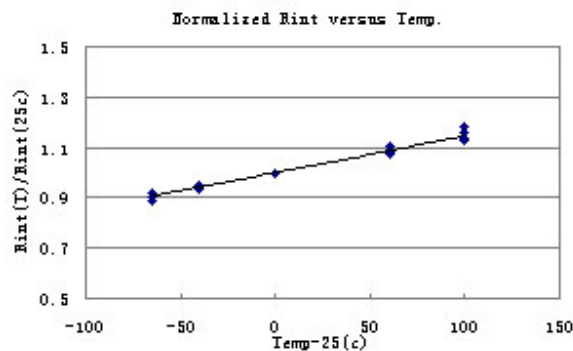
Fit.D8(c) Simulated(lines) and measured(symbols) resistance which normalized to Rsh(V=0) versus voltage.



Fit.D8(d) Sheet resistance which normalized to Rsh(T=25C) for various widths. (Tc1 = 1.41E-03, Tc2 = 6.87E-07)



Fit.D8(e) Interface resistance versus 1/Weff for the parameter of Rint0 and Rintc's extraction



Fit.D8(f) Interface resistance which normalized to Rint(T=25C) for various widths. (Rinttc1= 1.38E-03, Rinttc2 = 6.47E-07)

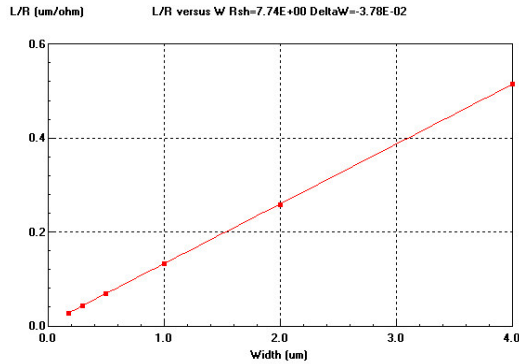
Fig.D8(a)(b)(c)(d)(e)(f) Fitting results of P+ Diffusion without silicide (non-standard) resistance model

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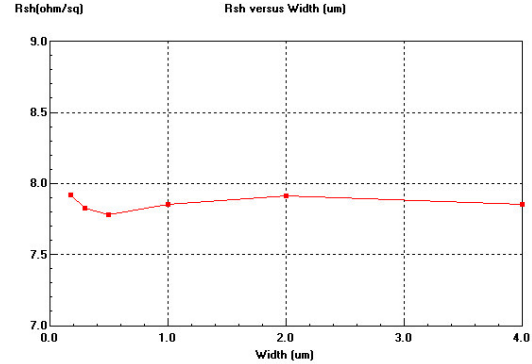


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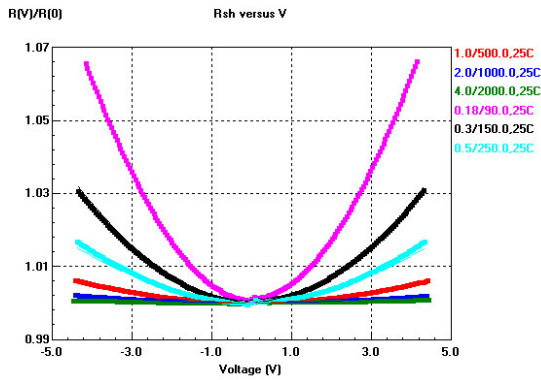
Doc. TD-LO18-SP-2003	No.:	Doc. Title: 0.18um Logic Low Leakage 1P6M (1P5M, 1P4M) Salicide 1.8V/5.0V SPICE Model (Version 1.3)	Doc. Rev: 4R	Tech Dev Rev.:1.3	Page 9/21	No.:
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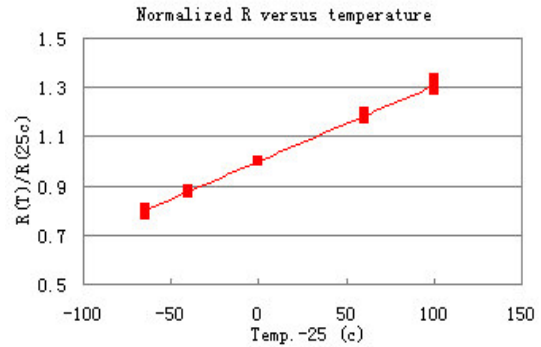
Fit.D9(a) Length/Resistance versus width for sheet resistance and delta width's extraction



Fit.D9(b) Extracted sheet resistance versus width for recommend width's selection



Fit.D9(c) Simulated(lines) and measured(symbols) resistance which normalized to Rsh(V=0) versus voltage.



Fit.D9(d) Sheet resistance which normalized to Rsh(T=25C) for various widths.
(Tc1 = 3.07E-03, Tc2 = -5.36E-08)

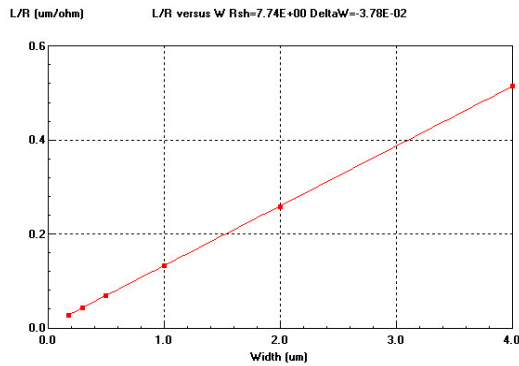
Fig.D9(a)(b)(c)(d) Fitting results of N+ Poly with silicide resistance model

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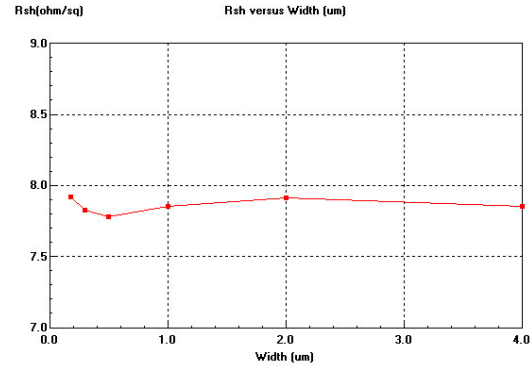


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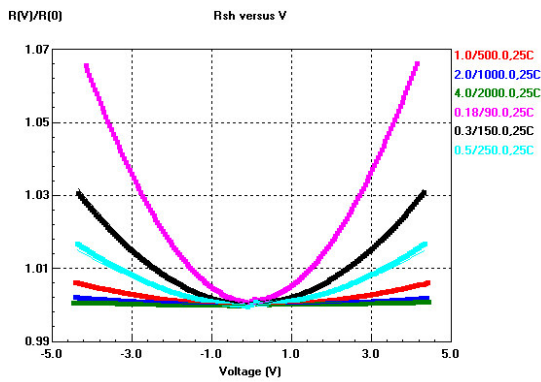
Doc. TD-LO18-SP-2003	No.:	Doc. Title: 0.18um Logic Low Leakage 1P6M (1P5M, 1P4M) Salicide 1.8V/5.0V SPICE Model (Version 1.3)	Doc. Rev: 4R	Tech Dev Rev.:1.3	Page No.: 10/21
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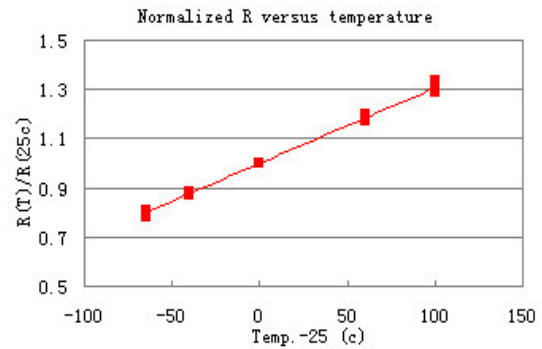
Fit.D10(a) Length/Resistance versus width for sheet resistance and delta width's extraction



Fit.D10(b) Extracted sheet resistance versus width for recommend width's selection



Fit.D10(c) Simulated(lines) and measured(symbols) resistance which normalized to Rsh(V=0) versus voltage.



Fit.D10(d) Sheet resistance which normalized to Rsh(T=25C) for various widths. (Tc1 = 3.07E-03, Tc2 = -5.36E-08)

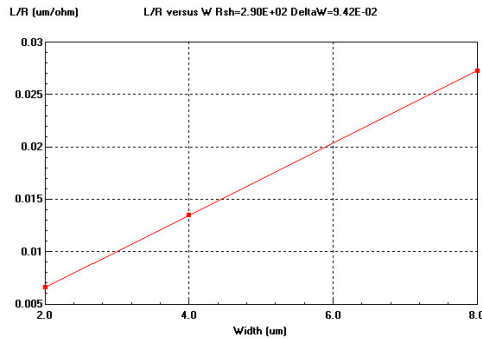
Fig.D10(a)(b)(c)(d) Fitting results of N+ Poly_3T with silicide resistance model

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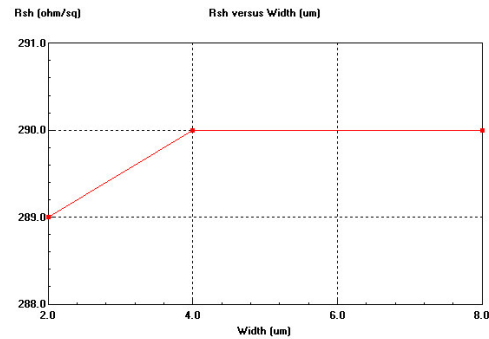


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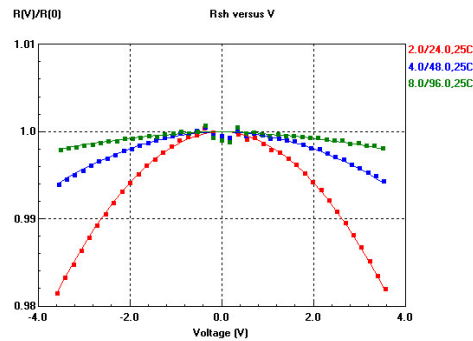
Doc. No.: TD-LO18-SP-2003	Doc. Title: 0.18um Logic Low Leakage 1P6M (1P5M, 1P4M) Salicide 1.8V/5.0V SPICE Model (Version 1.3)	Doc. Rev: 4R	Tech Dev Rev.:1.3	Page No.: 11/21
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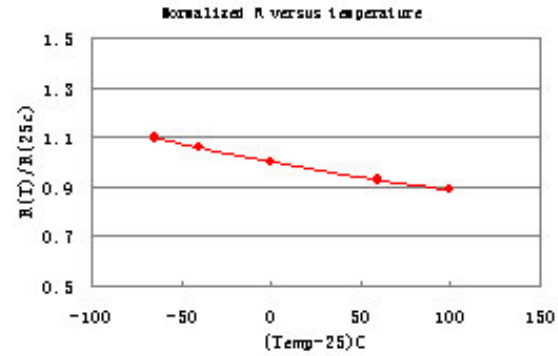
Fit.D11(a) Length/Resistance versus width for sheet resistance and delta width's extraction



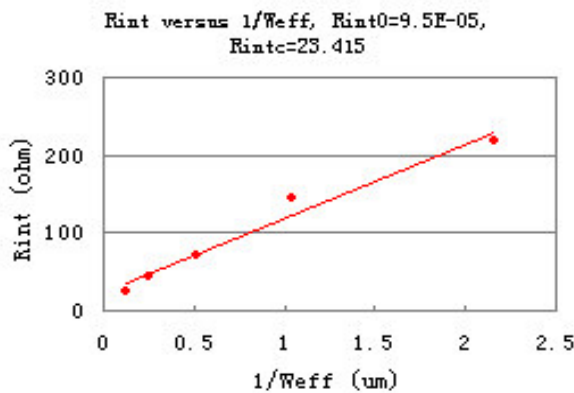
Fit.D11(b) Extracted sheet resistance versus width for recommend width's selection



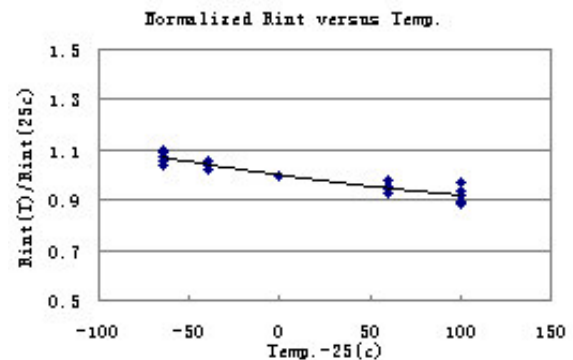
Fit.D11(c) Simulated(lines) and measured(symbols) resistance which normalized to $R_{sh}(V=0)$ versus voltage.



Fit.D11(d) Sheet resistance which normalized to $R_{sh}(T=25C)$ for various widths. ($T_{c1} = -1.35E-03$, $T_{c2} = 2.29E-06$)



Fit.D11(e) Interface resistance versus $1/W_{eff}$ for the parameter of R_{int0} and R_{intc} 's extraction



Fit.D11(f) Interface resistance which normalized to $R_{int}(T=25C)$ for various widths. ($R_{inttc1} = -9.76E-04$, $R_{inttc2} = 1.70E-06$)

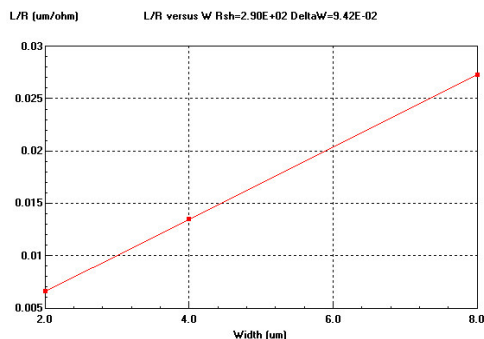
Fig.D11(a)(b)(c)(d)(e)(f) Fitting results of N+ Poly without silicide resistance model

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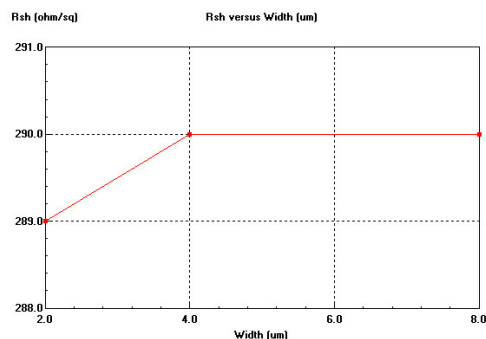


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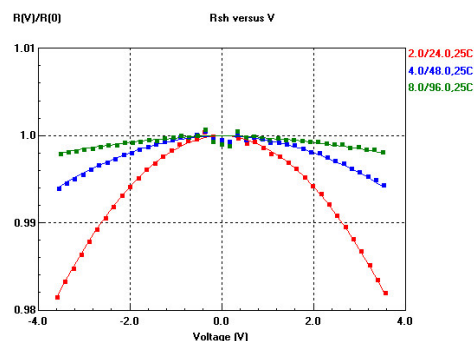
Doc. TD-LO18-SP-2003	No.: Doc. Title: 0.18um Logic Low Leakage 1P6M (1P5M, 1P4M) Salicide 1.8V/5.0V SPICE Model (Version 1.3)	Doc. Rev: 4R	Tech Dev Rev.:1.3	Page 12/21	No.:
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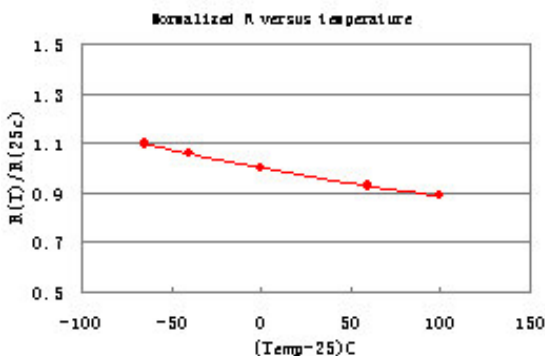
Fit.D12(a) Length/Resistance versus width for sheet resistance and delta width's extraction



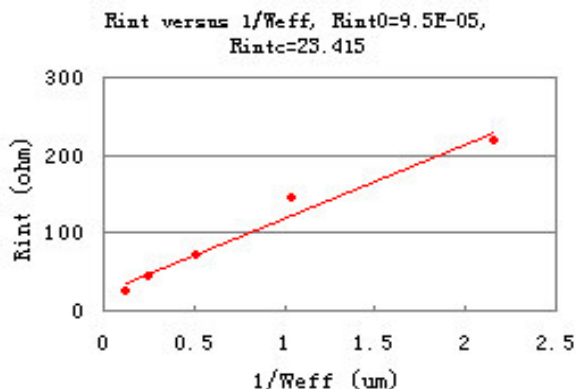
Fit.D12(b) Extracted sheet resistance versus width for recommend width's selection



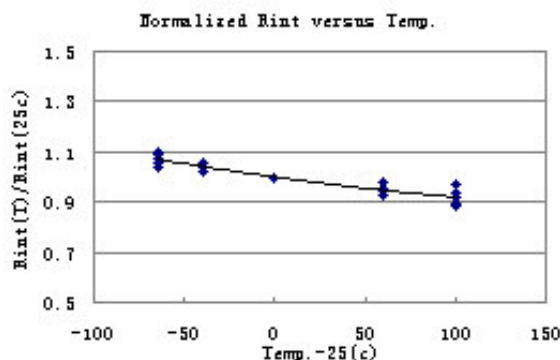
Fit.D12(c) Simulated(lines) and measured(symbols) resistance which normalized to $R_{sh}(V=0)$ versus voltage.



Fit.D12(d) Sheet resistance which normalized to $R_{sh}(T=25C)$ for various widths.
($T_{c1} = -1.35E-03$, $T_{c2} = 2.29E-06$)



Fit.D12(e) Interface resistance versus $1/W_{eff}$ for the parameter of R_{int0} and R_{intc} 's extraction



Fit.D12(f) Interface resistance which normalized to $R_{int}(T=25C)$ for various widths.
($R_{inttc1} = -9.76E-04$, $R_{inttc2} = 1.70E-06$)

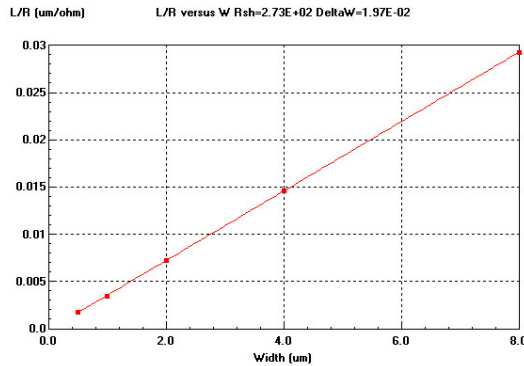
Fig.D12(a)(b)(c)(d)(e)(f) Fitting results of N+ Poly_3T without silicide resistance model

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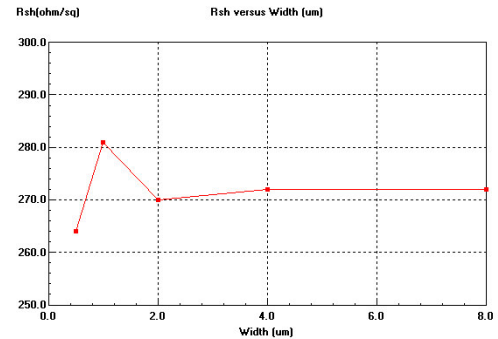


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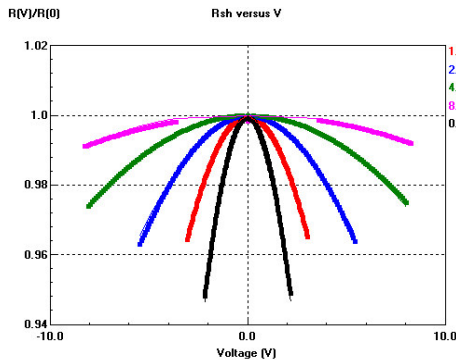
Doc. TD-LO18-SP-2003	No.: Doc. Title: 0.18um Logic Low Leakage 1P6M (1P5M, 1P4M) Salicide 1.8V/5.0V SPICE Model (Version 1.3)	Doc. Rev: 4R	Tech Dev Rev.:1.3	Page 13/21	No.:
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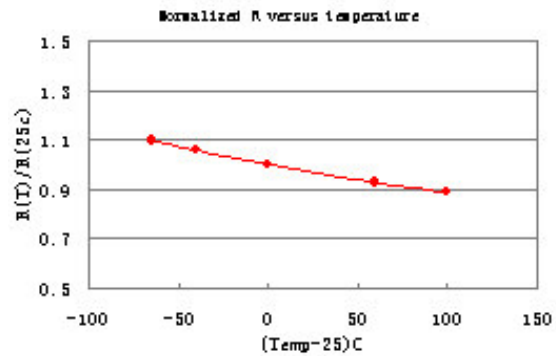
Fit.D13(a) Length/Resistance versus width for sheet resistance and delta width's extraction



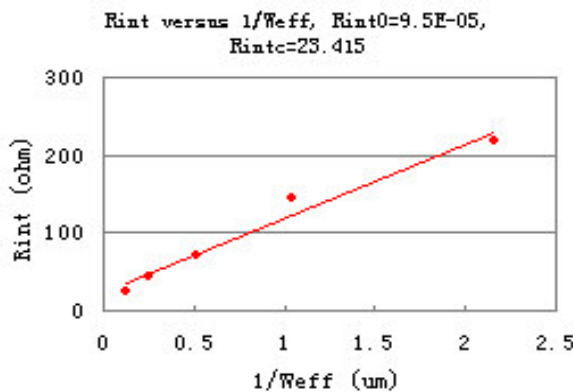
Fit.D13(b) Extracted sheet resistance versus width for recommend width's selection



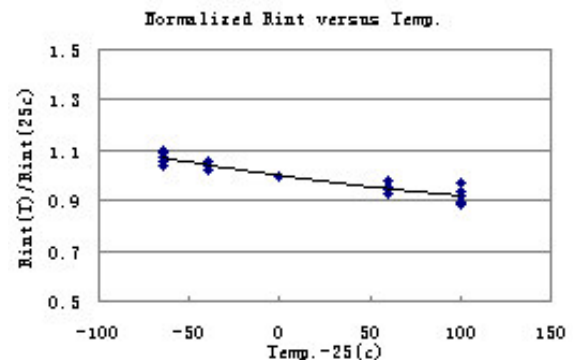
Fit.D13(c) Simulated(lines) and measured(symbols) resistance which normalized to Rsh(V=0) versus voltage.



Fit.D13(d) Sheet resistance which normalized to Rsh(T=25C) for various widths.
(Tc1 = -1.35E-03, Tc2 = 2.29E-06)



Fit.D13(e) Interface resistance versus 1/Weff for the parameter of Rint0 and Rintc's extraction



Fit.D13(f) Interface resistance which normalized to Rint(T=25C) for various widths.
(Rinttc1 = -9.76E-04, Rinttc2 = 1.70E-06)

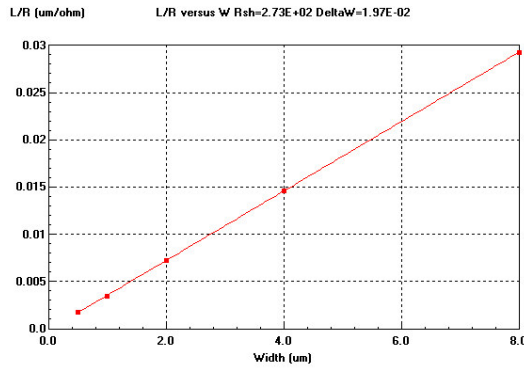
Fig.D13(a)(b)(c)(d)(e)(f) Fitting results of N+ Poly without silicide (non-standard) resistance model

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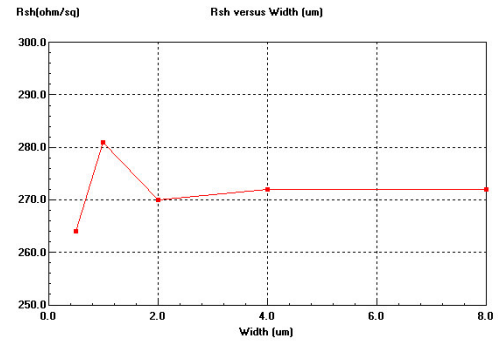


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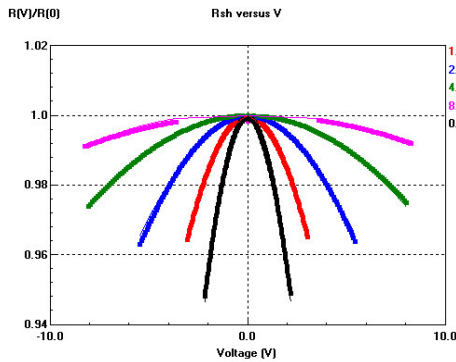
Doc. TD-LO18-SP-2003	No.: Doc. Title: 0.18um Logic Low Leakage 1P6M (1P5M, 1P4M) Salicide 1.8V/5.0V SPICE Model (Version 1.3)	Doc. Rev: 4R	Tech Dev Rev.:1.3	Page 14/21	No.:
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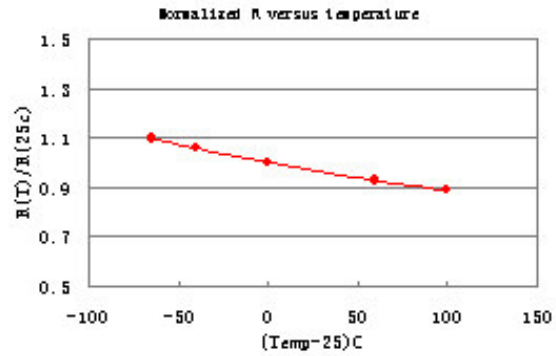
Fit.D14(a) Length/Resistance versus width for sheet resistance and delta width's extraction



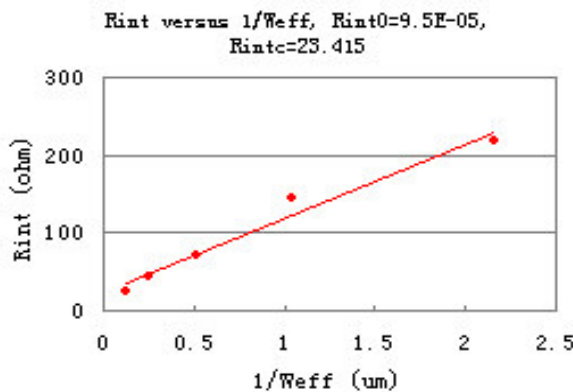
Fit.D14(b) Extracted sheet resistance versus width for recommend width's selection



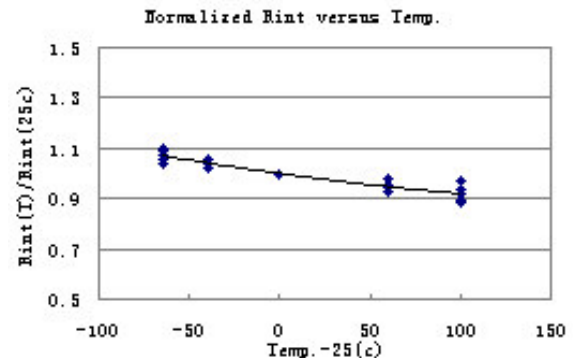
Fit.D14(c) Simulated(lines) and measured(symbols) resistance which normalized to Rsh(V=0) versus voltage.



Fit.D14(d) Sheet resistance which normalized to Rsh(T=25C) for various widths.
(Tc1 = -1.35E-03, Tc2 = 2.29E-06)



Fit.D14(e) Interface resistance versus 1/Weff for the parameter of Rint0 and Rintc's extraction



Fit.D14(f) Interface resistance which normalized to Rint(T=25C) for various widths.
(Rinttc1 = -9.76E-04, Rinttc2 = 1.70E-06)

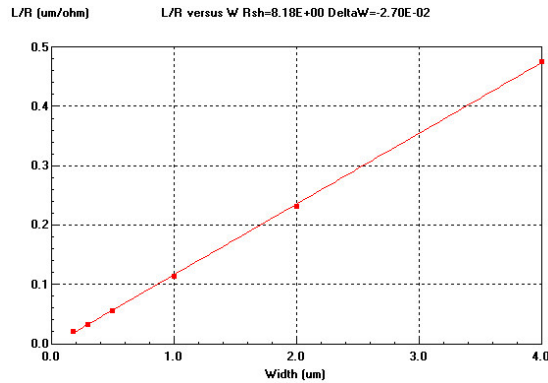
Fig.D14(a)(b)(c)(d)(e)(f) Fitting results of N+ Poly_3T without silicide (non-standard) resistance model

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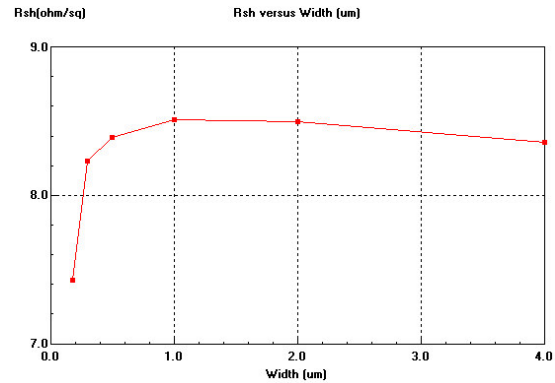


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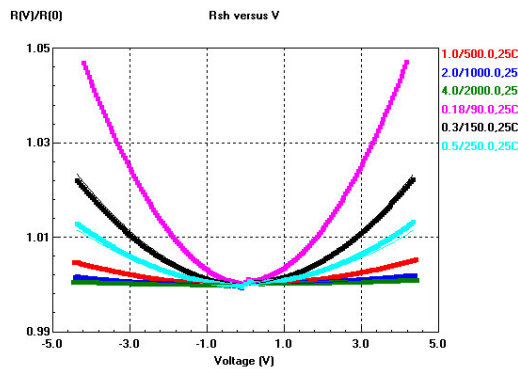
Doc. TD-LO18-SP-2003	No.: Doc. Title: 0.18um Logic Low Leakage 1P6M (1P5M, 1P4M) Salicide 1.8V/5.0V SPICE Model (Version 1.3)	Doc. Rev: 4R	Tech Dev Rev.:1.3	Page 15/21	No.:
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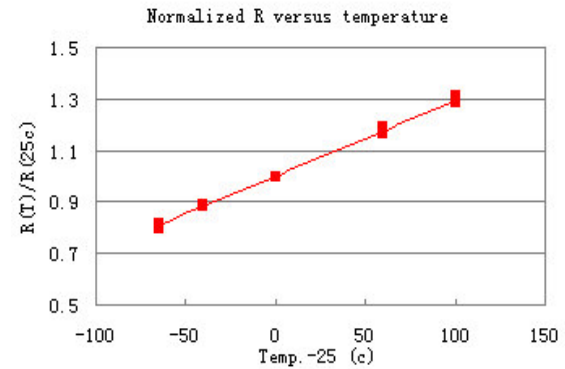
Fit.D15(a) Length/Resistance versus width for sheet resistance and delta width's extraction



Fit.D15(b) Extracted sheet resistance versus width for recommend width's selection



Fit.D15(c) Simulated(lines) and measured(symbols) resistance which normalized to Rsh(V=0) versus voltage.



Fit.D15(d) Sheet resistance which normalized to Rsh(T=25C) for various widths.
(Tc1 = 2.92E-03, Tc2 = -2.30E-08)

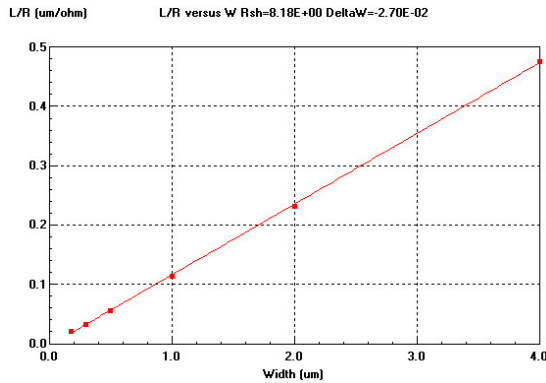
Fig.D15(a)(b)(c)(d) Fitting results of P+ Poly with silicide resistance model

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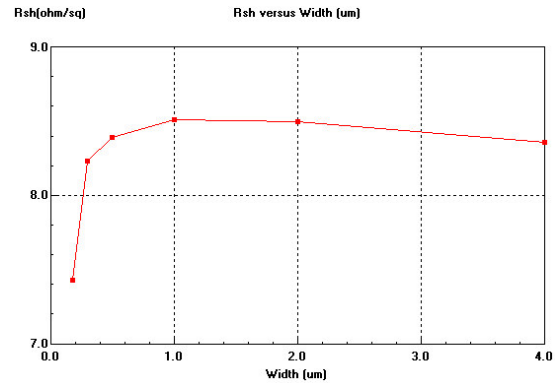


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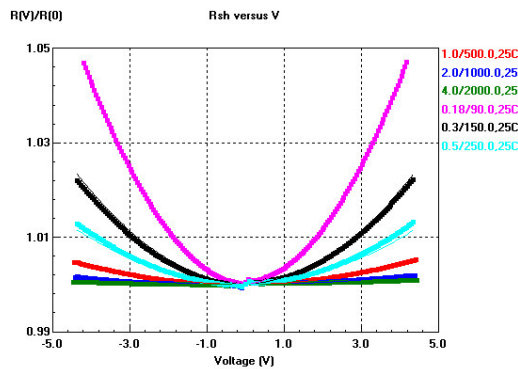
Doc. TD-LO18-SP-2003	No.: Doc. Title: 0.18um Logic Low Leakage 1P6M (1P5M, 1P4M) Salicide 1.8V/5.0V SPICE Model (Version 1.3)	Doc. Rev: 4R	Tech Dev Rev.:1.3	Page 16/21	No.:
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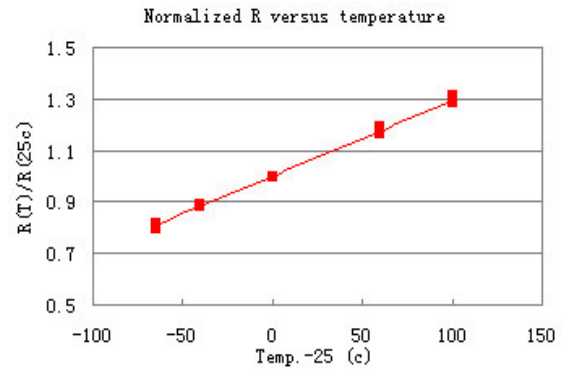
Fit.D16(a) Length/Resistance versus width for sheet resistance and delta width's extraction



Fit.D16(b) Extracted sheet resistance versus width for recommend width's selection



Fit.D16(c) Simulated(lines) and measured(symbols) resistance which normalized to Rsh(V=0) versus voltage.



Fit.D16(d) Sheet resistance which normalized to Rsh(T=25C) for various widths.
(Tc1 = 2.92E-03, Tc2 = -2.30E-08)

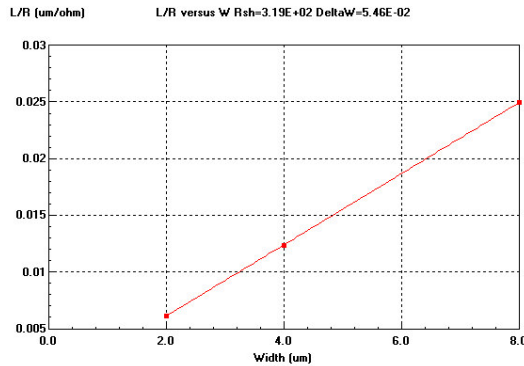
Fig.D16(a)(b)(c)(d) Fitting results of P+ Poly_3T with silicide resistance model

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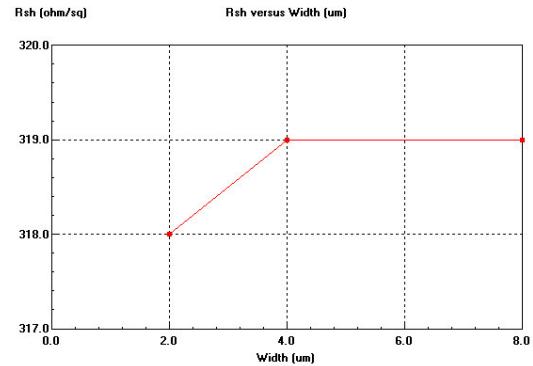


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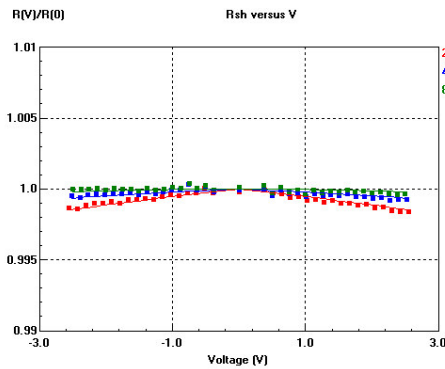
Doc. No.: TD-LO18-SP-2003	Doc. Title: 0.18um Logic Low Leakage 1P6M (1P5M, 1P4M) Salicide 1.8V/5.0V SPICE Model (Version 1.3)	Doc. Rev: 4R	Tech Dev Rev.:1.3	Page No.: 17/21
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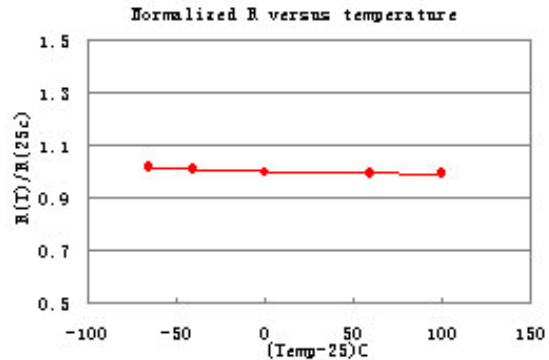
Fit.D17(a) Length/Resistance versus width for sheet resistance and delta width's extraction



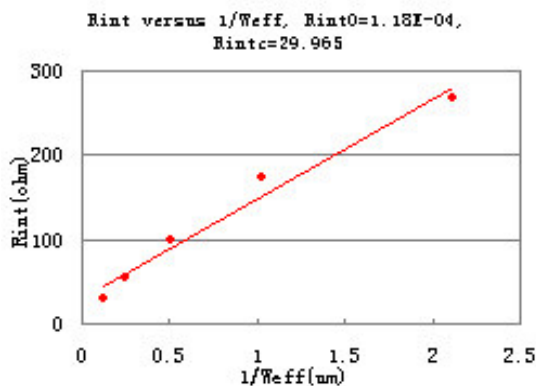
Fit.D17(b) Extracted sheet resistance versus width for recommend width's selection



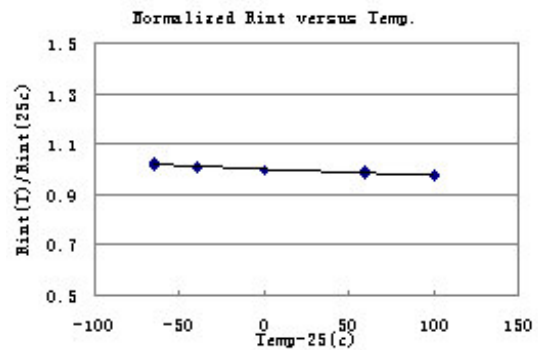
Fit.D17(c) Simulated(lines) and measured(symbols) resistance which normalized to Rsh(V=0) versus voltage.



Fit.D17(d) Sheet resistance which normalized to Rsh(T=25C) for various widths. (Tc1 = -1.63E-04, Tc2 = 7.46E-07)



Fit.D17(e) Interface resistance versus 1/Weff for the parameter of Rint0 and Rintc's extraction



Fit.D17(f) Interface resistance which normalized to Rint(T=25C) for various widths. (Rinttc1 = -2.76E-04, Rinttc2 = 3.25E-07)

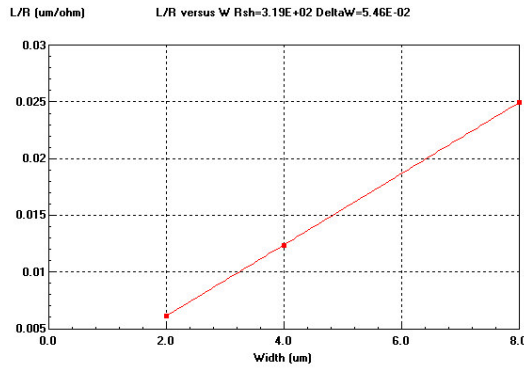
Fig.D17(a)(b)(c)(d)(e)(f) Fitting results of P+ Poly without silicide resistance model

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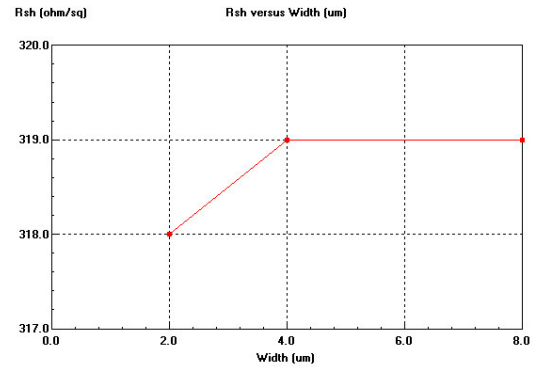


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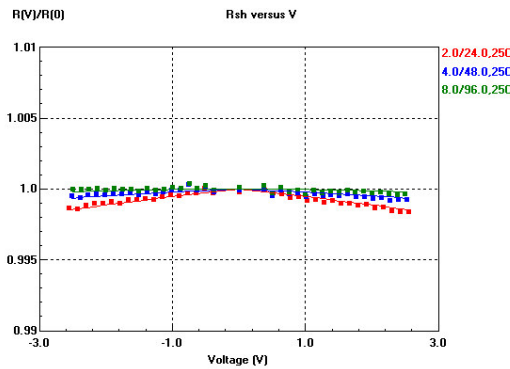
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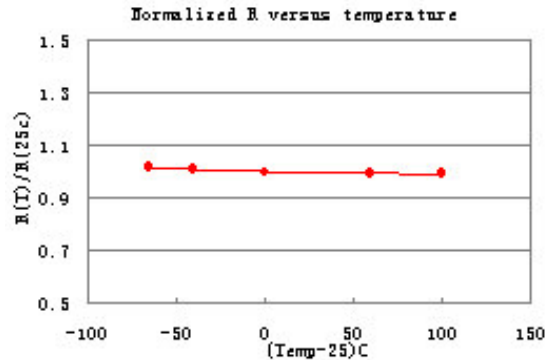
Fit.D18(a) Length/Resistance versus width for sheet resistance and delta width's extraction



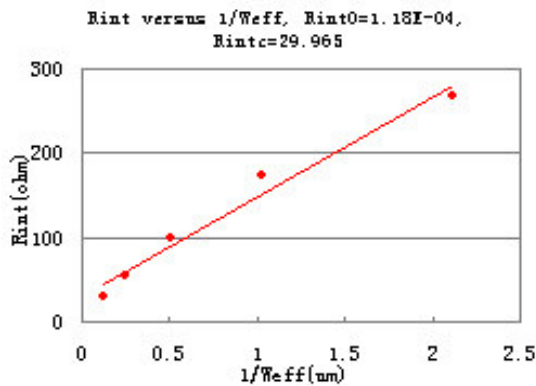
Fit.D18(b) Extracted sheet resistance versus width for recommend width's selection



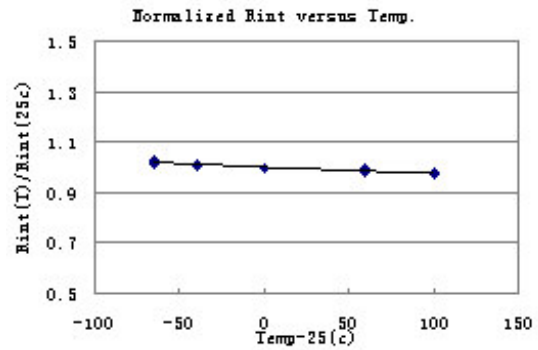
Fit.D18(c) Simulated(lines) and measured(symbols) resistance which normalized to Rsh(V=0) versus voltage.



Fit.D18(d) Sheet resistance which normalized to Rsh(T=25C) for various widths. (Tc1 = -1.63E-04, Tc2 = 7.46E-07)



Fit.D18(e) Interface resistance versus 1/Weff for the parameter of Rint0 and Rintc's extraction



Fit.D18(f) Interface resistance which normalized to Rint(T=25C) for various widths. (Rinttc1 = -2.76E-04, Rinttc2 = 3.25E-07)

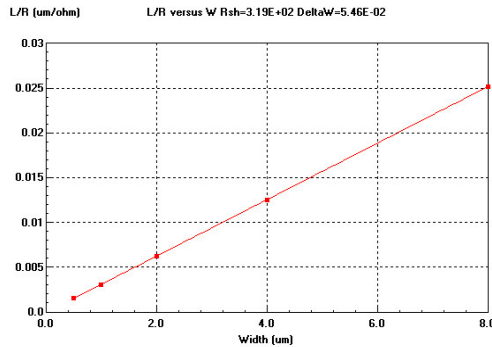
Fig.D18(a)(b)(c)(d)(e)(f) Fitting results of P+ Poly_3T without silicide resistance model

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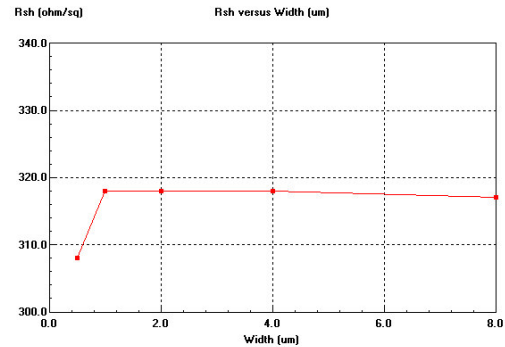


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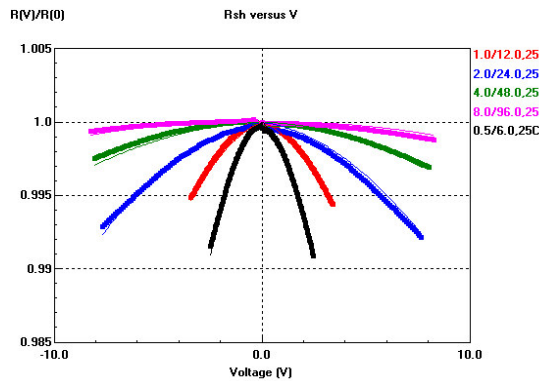
Doc. No.: TD-LO18-SP-2003	Doc. Title: 0.18um Logic Low Leakage 1P6M (1P5M, 1P4M) Salicide 1.8V/5.0V SPICE Model (Version 1.3)	Doc. Rev: 4R	Tech Dev Rev.:1.3	Page No.: 19/21
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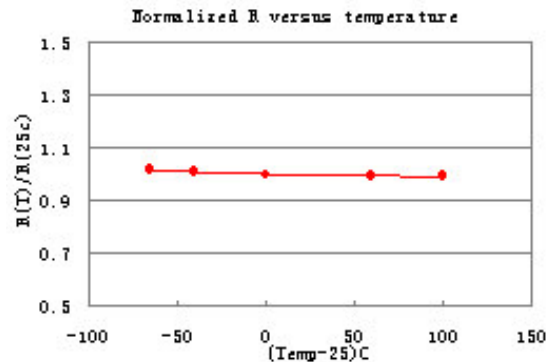
Fit.D19(a) Length/Resistance versus width for sheet resistance and delta width's extraction



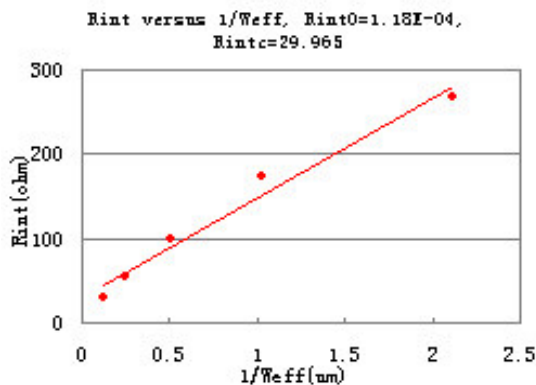
Fit.D19(b) Extracted sheet resistance versus width for recommend width's selection



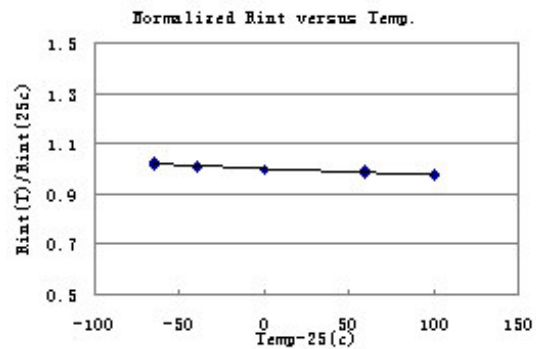
Fit.D19(c) Simulated(lines) and measured(symbols) resistance which normalized to Rsh(V=0) versus voltage.



Fit.D19(d) Sheet resistance which normalized to Rsh(T=25C) for various widths.
(Tc1 = -1.63E-04, Tc2 = 7.46E-07)



Fit.D19(e) Interface resistance versus 1/Weff for the parameter of Rint0 and Rintc's extraction



Fit.D19(f) Interface resistance which normalized to Rint(T=25C) for various widths.
(Rinttc1 = -2.76E-04, Rinttc2 = 3.25E-07)

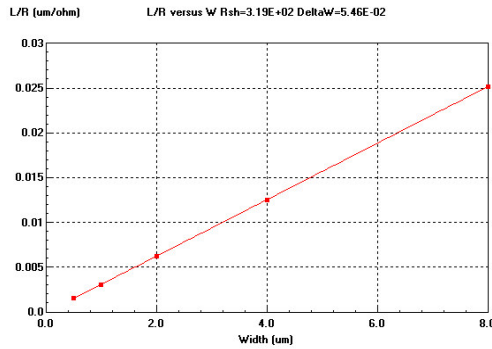
Fig.D19(a)(b)(c)(d)(e)(f) Fitting results of P+ Poly without silicide (non-standard) resistance model

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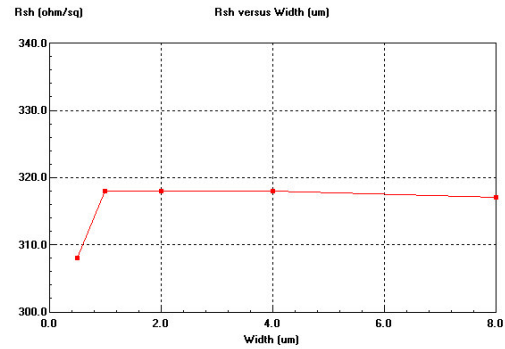


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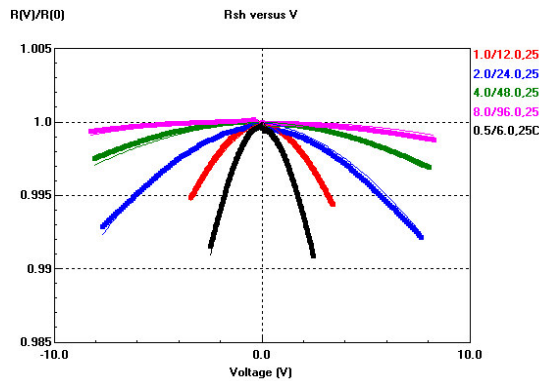
Doc. No.: TD-LO18-SP-2003	Doc. Title: 0.18um Logic Low Leakage 1P6M (1P5M, 1P4M) Salicide 1.8V/5.0V SPICE Model (Version 1.3)	Doc. Rev: 4R	Tech Dev Rev.:1.3	Page No.: 20/21
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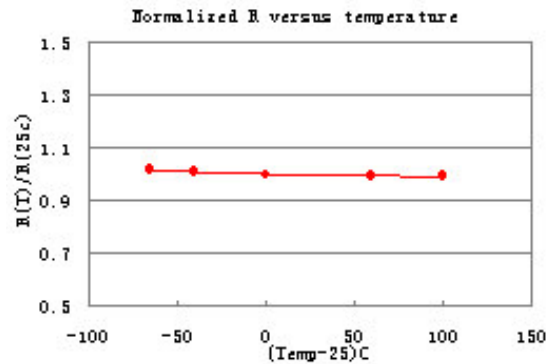
Fit.D20(a) Length/Resistance versus width for sheet resistance and delta width's extraction



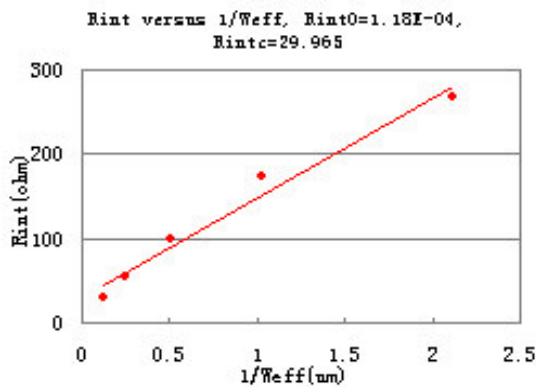
Fit.D20(b) Extracted sheet resistance versus width for recommend width's selection



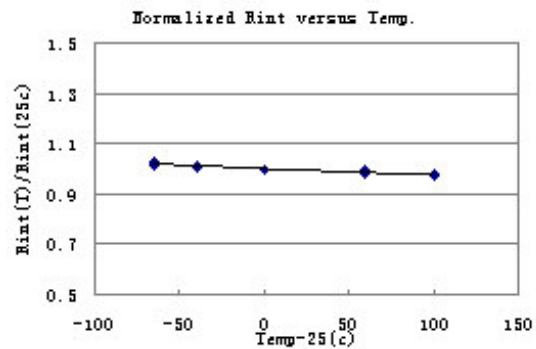
Fit.D20(c) Simulated (lines) and measured (symbols) resistance which normalized to Rsh(V=0) versus voltage.



Fit.D20(d) Sheet resistance which normalized to Rsh(T=25C) for various widths. (Tc1 = -1.63E-04, Tc2 = 7.46E-07)



Fit.D20(e) Interface resistance versus 1/Weff for the parameter of Rint0 and Rintc's extraction



Fit.D20(f) Interface resistance which normalized to Rint(T=25C) for various widths. (Rinttc1 = -2.76E-04, Rinttc2 = 3.25E-07)

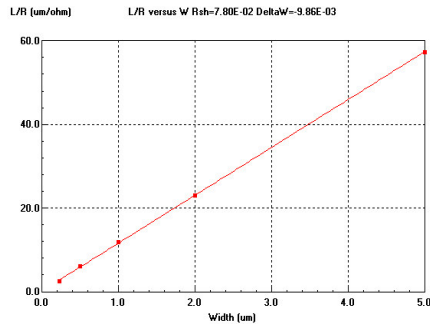
Fig.D20(a)(b)(c)(d)(e)(f) Fitting results of P+ Poly_3T without silicide (non-standard) resistance model

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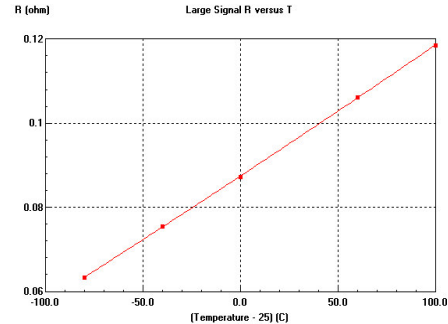


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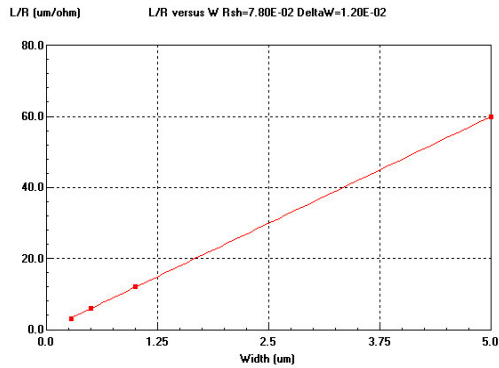


Fit.D21(a) Length/Resistance versus width for sheet resistance and delta width's extraction

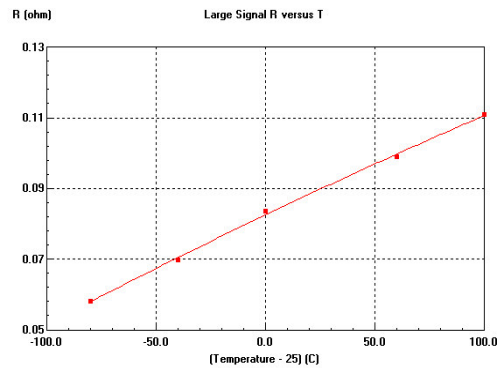


Fit.D21(b) Sheet resistance which normalized to Rsh(T=25C) for various widths (Tc1 = 3.49E-03, Tc2 = 6.93E-07)

Fig.D21(a)(b) Fitting results of Metal1 resistance model

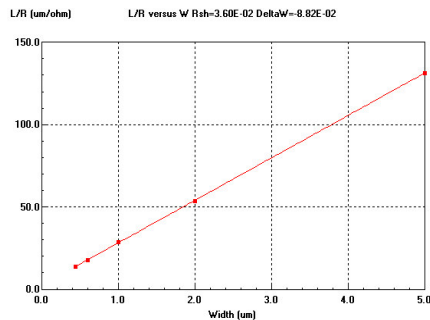


Fit.D22(a) Length/Resistance versus width for sheet resistance and delta width's extraction

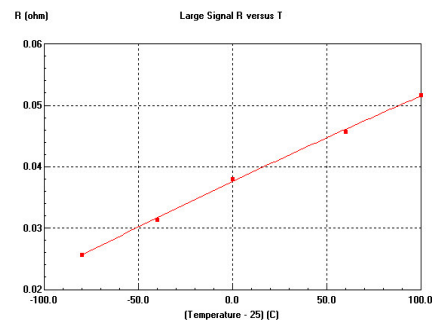


Fit.D22(b) Sheet resistance which normalized to Rsh(T=25C) for various widths (Tc1 = 3.60E-03, Tc2 = 7.60E-07)

Fig.D22(a)(b) Fitting results of Metal2, Metal3, Metal4 and Metal5 resistance model



Fit.D23(a) Length/Resistance versus width for sheet resistance and delta width's extraction



Fit.D23(b) Sheet resistance which normalized to Rsh(T=25C) for various widths (Tc1 = 3.89E-03, Tc2 = 1.01E-06)

Fig.D23(a)(b) Fitting results of Metal6 resistance model

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